Product data sheet

1. General description

Planar passivated very sensitive gate four quadrant triac in a TO92 plastic package intended for interfacing with low power drivers including microcontrollers.

2. Features and benefits

- · Direct interfacing to logic level ICs
- · Direct interfacing with low power gate drivers and microcontrollers
- High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Very sensitive gate

3. Applications

- · Air conditioner indoor fan
- General purpose low power motor control
- · General purpose switching and phase control

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
V_{DRM}	repetitive peak off-state voltage			8	800		V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 51 °C; <u>Fig. 1; Fig. 2; Fig. 3</u>			1		А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	12.5			А	
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms				А	
T _j	junction temperature			125			°C
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	0.4	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$		-	1.3	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. } 7$		-	1.4	3	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2- \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	3.8	7	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>		-	1.3	5	mA
V _T	on-state voltage	I _T = 1.4 A; T _i = 25 °C; <u>Fig. 10</u>		-	1.2	1	V

4Q Triac

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; $R_{GT1(ext)}$ = 1 k Ω ; Fig. 12	10	20	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; dI_{com}/dt = 0.5 \text{ A/ms};$ $I_T = 1 \text{ A}; gate open circuit}$	2	-	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		
2	G	gate		Ν
3	T1	main terminal 1	TO-92 (SOT54)	T2 — T1 G sym051

6. Ordering information

Table 3. Ordering information

Table 6. Grading information						
Type number	Package	e				
	Name	Description	Version			
BT131-800	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54			

7. Marking

Table 4. Marking codes

Type number	Marking codes
BT131-800	131-8

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage [1]		800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 51 °C; <u>Fig 1</u> ; <u>Fig 2</u> ; <u>Fig 3</u>	1	Α
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig 4; Fig 5	12.5	А
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$	13.7	Α
l²t	I ² t for fusing	t _P = 10 ms; sine-wave pulse	0.78	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 6 mA; T2+ G+	50	A/µs
		I _G = 6 mA; T2+ G-	50	A/µs
		I _G = 6 mA; T2- G-	50	A/µs
		I _G = 14 mA; T2- G+	10	A/µs
I _{GM}	peak gate current		2	Α
P _{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.1	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		125	°C

[1] Although not recommended, off-state voltage up to V_{DRM} may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed $3A/\mu s$.

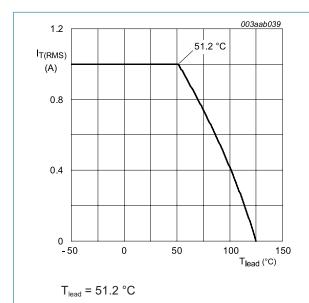


Fig. 1. RMS on-state current as a function of lead temperature; maximum values

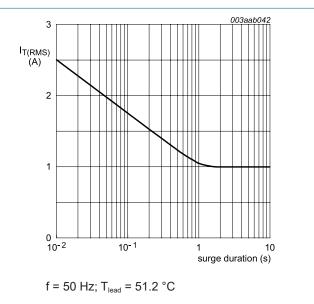


Fig. 2. RMS on-state current as a function of surge duration; maximum values

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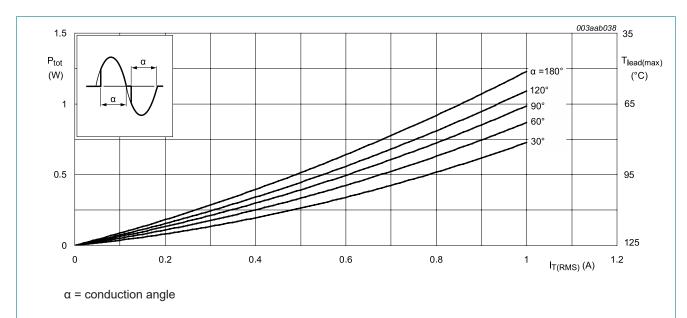


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

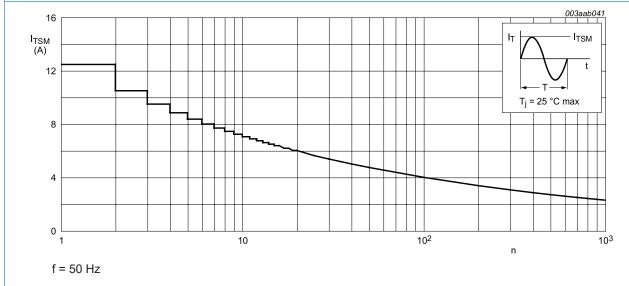
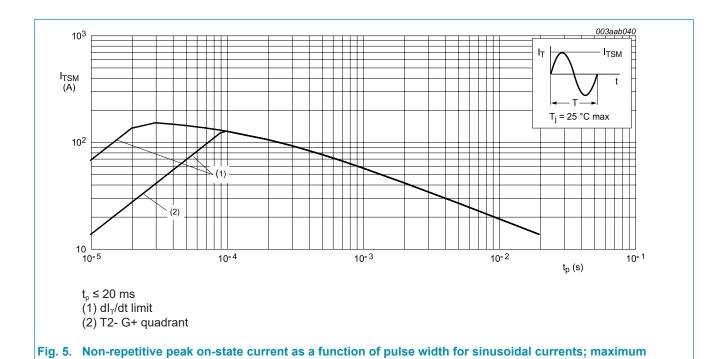


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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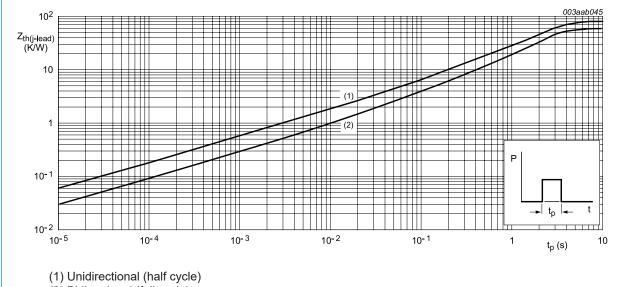
values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance	full cycle; Fig 6	-	-	60	K/W
	from junction to lead	half cycle; <u>Fig 6</u>	-	-	80	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



(2) Bidirectional (full cycle)

Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

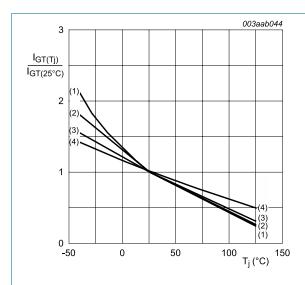
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	0.4	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	-	1.3	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	1.4	3	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	3.8	7	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	1.2	5	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 8}}$	-	4	8	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	1	5	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	2.5	8	mA
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; Fig. 9$	-	1.3	5	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.2	0.3	-	V
I_D	off-state current	$V_D = 800 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	0.1	0.5	mA
Dynamic	characteristics		·			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; $(V_{DM}$ = 67% of V_{DRM}); exponential waveform; $R_{GT1(ext)}$ = 1 kΩ; Fig. 12	10	20	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; dI_{com}/dt = 0.5 \text{ A/}$ ms; $I_T = 1 \text{ A};$ gate open circuit	2	-	-	V/µs
t _{gt}	gate-controlled turn-on time	$I_{TM} = 1.5 \text{ A}; V_D = 800 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

4Q Triac



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

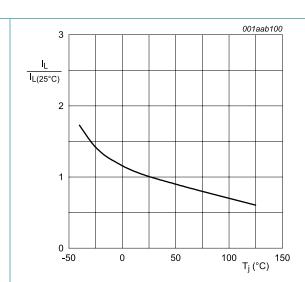


Fig. 8. Normalized latching current as a function of junction temperature

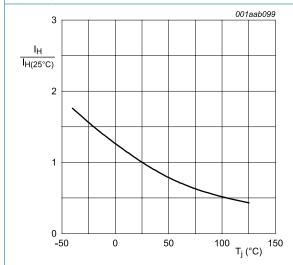
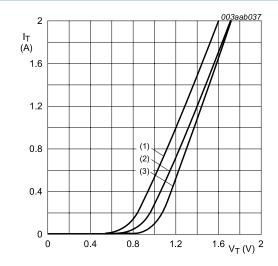


Fig. 9. Normalized holding current as a function of junction temperature



 $V_o = 0.92 \text{ V}; R_s = 0.4 \Omega$

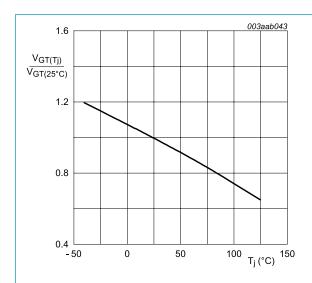
(1) T_i = 125 °C; typical values

(2) T_j = 125 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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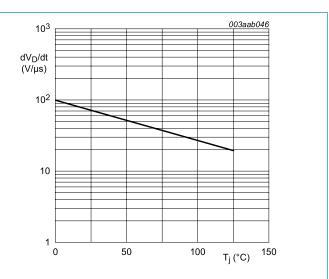
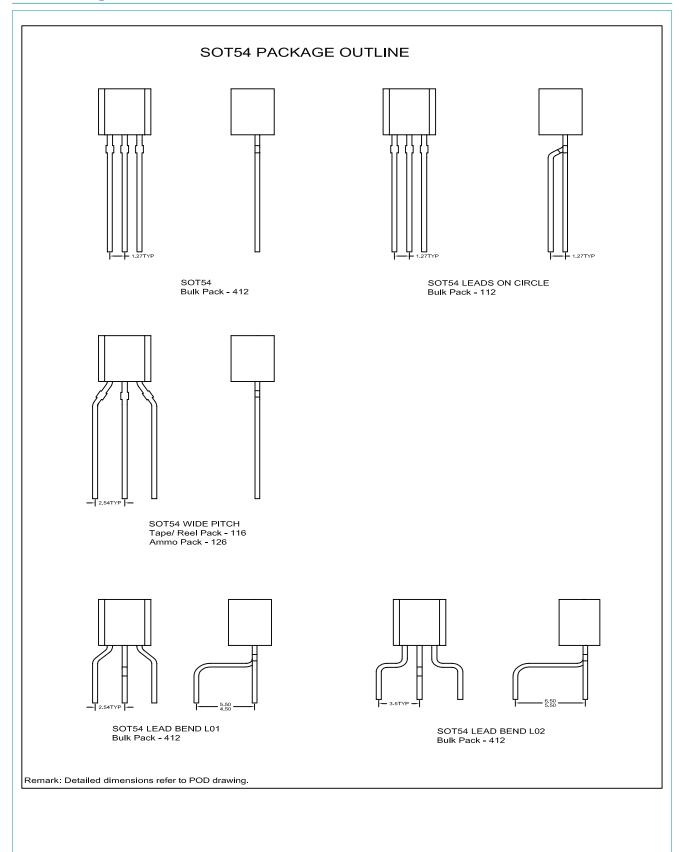


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

Fig. 12. Rate of rise of off-state voltage as a function of junction temperature; typical values

4Q Triac

11. Package outline



4Q Triad

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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4Q Triac

13. Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	6
10. Characteristics	7
11. Package outline	10
12. Legal information	11
13. Contents	13

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